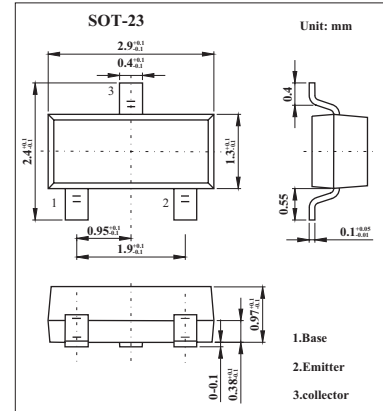


PNP Epitaxial Planar Silicon Transistors

2SA1252



■ Features

- High V_{EBO} .
- Wide ASO and high durability against breakdown.

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-60	V
Collector-emitter voltage	V_{CEO}	-50	V
Emitter-base voltage	V_{EBO}	-15	V
Collector current	I_C	-150	mA
Collector current (pulse)	I_{CP}	-300	mA
Collector dissipation	P_C	200	mW
Jumction temperature	T_j	125	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +125	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector cutoff current	I_{CBO}	$V_{CB} = -40\text{V}$, $I_E = 0$			-0.1	μA
Emitter cutoff current	I_{EBO}	$V_{EB} = -10\text{V}$, $I_C = 0$			-0.1	μA
DC current Gain	h_{FE}	$V_{CE} = -6\text{V}$, $I_C = -1\text{mA}$	90		560	
Gain bandwidth product	f_T	$V_{CE} = -6\text{V}$, $I_C = -1\text{mA}$		100		MHz
Output capacitance	C_{ob}	$V_{CB} = -6\text{V}$, $f = 1\text{MHz}$		3.5		pF
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -50\text{mA}$, $I_B = -5\text{mA}$			-0.5	V
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -10\mu\text{A}$, $I_E = 0$	-60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1\text{mA}$, $R_{BE} = \infty$	-50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -10\mu\text{A}$, $I_C = 0$	-15			V

■ h_{FE} Classification

Marking	D4	D5	D6	D7
h_{FE}	90~180	135~270	200~400	300~600